rfmd.com

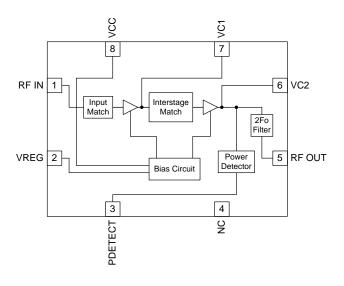
RoHS Compliant & Pb-Free Product Package Style: QFN, 8-Pin, 2x2x0.45mm

# **Features**

- Single Power Supply 3.0V to 4.5V
- 30dB Typical Gain, Input Matched to 50Ω
- 2.4 GHz to 2.5 GHz Frequency Range
- 11g P<sub>OUT</sub>=+18dBm@3% Typ EVM, 95 mA

## **Applications**

- IEEE802.11b/g/n WLAN Applications
- 2.5 GHz ISM Band Applications
- Commercial and Consumer Systems
- Portable Battery-Powered Equipment
- Spread-Spectrum and MMDS Systems



Functional Block Diagram

## **Product Description**

The RF5622 is a linear, medium-power, high-efficiency, two-stage amplifier IC designed specifically for battery-powered WLAN applications such as PC cards, mini PCI, and compact flash applications. The device is manufactured on an advanced InGaP Gallium Arsenide Heterojunction Bipolar Transistor (HBT) process, and has been designed for use as the final RF amplifier in 2.5 GHz OFDM and other spread-spectrum transmitters. The device is provided in a 2mmx2mm, 8-pin, QFN with a backside ground. The RF5622 is designed to maintain linearity over a wide range of supply voltage and power output. The RF5622 also has built-in power detector and incorporates the input and interstage matching components internally which reduces the component count used externally and makes it easier to incorporate on any design.

#### **Ordering Information**

RF5622 3.0V to 4.5V, 2.4GHz to 2.5GHz Linear Power Amplifier RF5622PCBA-41X Fully Assembled Evaluation Board

## **Optimum Technology Matching® Applied**

☐ GaAs HBT	☐ SiGe BiCMOS	☐ GaAs pHEMT	☐ GaN HEMT
☐ GaAs MESFET ✓ InGaP HBT	☐ Si BiCMOS	☐ Si CMOS	
▼ InGaP HBT	☐ SiGe HBT	☐ Si BJT	



# Preliminary



Please contact RFMD Technical Support at (336) 678-5570 for more information.